

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

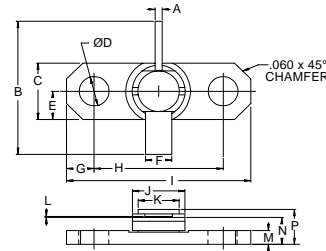
The **ASI OSC-1.3SH** is Designed for General Purpose Oscillator Applications up to 2.7 GHz.

**FEATURES:**

- $V_{CC} = 21\text{ V}$
- Common Collector
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	700 mA
$V_{CC}$	30 V
$P_{DISS}$	17.6 W @ $T_C \leq 50\text{ }^\circ\text{C}$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +200 °C
$\theta_{JC}$	8.5 °C/W

**PACKAGE STYLE .230 2L FLG**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E		.125 / 3.18
F	.110 / 2.79	.117 / 2.97
G		.117 / 2.97
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

**ORDER CODE: ASI10638**
**CHARACTERISTICS**  $T_C = 25\text{ }^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 1.0\text{ mA}$	45			V
$BV_{CER}$	$I_C = 5.0\text{ mA}$ $R_{BE} = 10\ \Omega$	45			V
$BV_{EBO}$	$I_E = 1.0\text{ mA}$	3.5			V
$I_{CBO}$	$V_{CB} = 28\text{ V}$			0.5	mA
$h_{FE}$	$V_{CE} = 5.0\text{ V}$ $I_C = 500\text{ mA}$	30		300	---
$C_{OB}$	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			12	pF
$P_G$ $\eta_C$	$V_{CC} = 21\text{ V}$ $I_{CQ} = 200\text{ mA}$ $f = 2.7\text{ GHz}$ $P_{OUT} = 1.3\text{ W}$	4.5	30		dB %